



## TO-92 Plastic-Encapsulated Transistors

### **2N4403** TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$$P_{CM} : 0.625 \text{ W (Tamb=25°C)}$$

Collector current

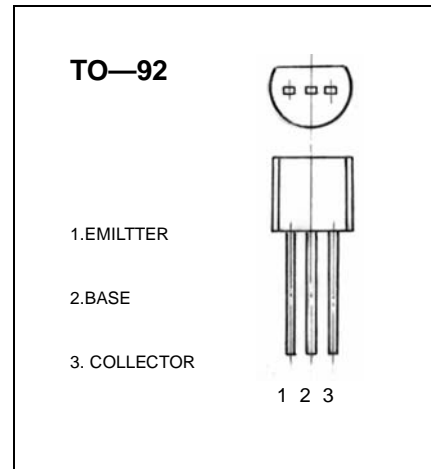
$$I_{CM} : -0.6 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -40 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



#### **ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -35 \text{ V}, I_E = 0$		-0.1	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CE} = -35 \text{ V}, I_B = 0$		-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4\text{V}, I_C = 0$		-0.1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE} = -2 \text{ V}, I_C = -150\text{mA}$	100	300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -150 \text{ mA}, I_B = -15\text{mA}$		-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -150 \text{ mA}, I_B = -15\text{mA}$		-0.95	V
Transition frequency	$f_T$	$V_{CE} = -10\text{V}, I_C = -20\text{mA}$ $f = 100\text{MHz}$	200		MHz